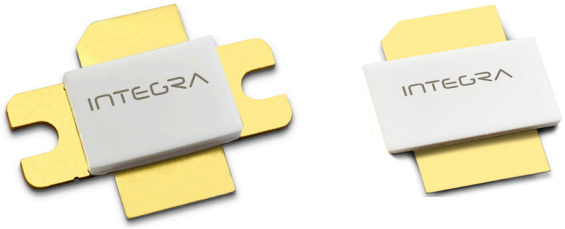
S-Band, GaN/SiC, RF Power Transistor

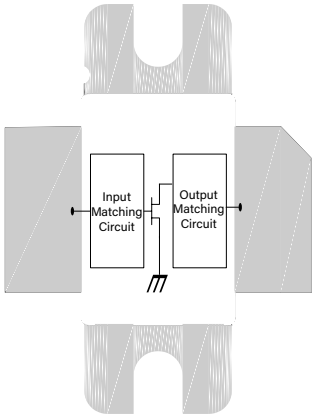
2.9 - 3.1 GHz | 800W | 48% Efficiency typ | 14 dB Gain typ | 80 V | 300µs Pulse Length, 15% Duty Cycle

IGN2931M800 and IGN2931M800S are high power GaN-on-SiC RF power transistors that have been designed to suit the unique needs of modern radar systems. They supply a minimum of 800W of peak output power, with typically 14dB of gain and 48% efficiency. They operate from a 80V supply voltage. For optimal thermal efficiency, the transistors are housed in a metal-based package with an epoxy-sealed ceramic lid.



FEATURES

- GaN on SiC HEMT Technology
- Output Power >800W
- Pre-matched Input and Output Impedances
- High Efficiency - 48% typical
- 100% RF Tested under 300µs, 15% duty cycle pulse conditions
- RoHS and REACH Compliant



APPLICATIONS

- S-band Radar Systems

Table 1. RF Electrical Characteristics (Case temperature = 30 °C unless otherwise stated)

Parameter	Symbol	Min	Typ	Max	Units	Test Conditions
Gain	G	12.5	14	15.5	dB	P_{OUT} = 800W f = 2.9, 3.0, 3.1 GHz 300µs pulse length, 15% duty cycle V_{DS} = 80V, I_{DS} = 150mA
Drain Efficiency	η	40	48	55	%	
Pulse Droop	D	0	-0.7	-1.0	dB	
Input Return Loss	IRL	7	15	25	dB	
VSWR Mismatch Stability	VSWR-S	2:1				
VSWR Withstand	VSWR-LMT	5:1				

Note: Consult Integra Technologies Application Note 001 for information on how RF output power and pulse droop are measured.

Table 2. Absolute Maximum Ratings (Not Simultaneous)

Parameter	Symbol	Value	Units	Test Conditions
DC Drain-Source Voltage	V_{DS}	350	V	25 °C
DC Gate-Source Voltage	V_{GS}	-8 to +1	V	25 °C
DC Drain Current	I_D	72	A	25 °C
DC Gate Current	I_G	1.4	mA	25 °C
RF Input Power	$P_{RF,IN}$	50	W	25 °C
Operating Channel Temperature	T_{CH}	-55 to +225	°C	
Storage Temperature	T_{STG}	-55 to +150	°C	
Soldering Temperature	T_{SOLDER}	260 for 60s	°C	

Note: Operation outside the limits given in this table may cause permanent damage to the transistor

Table 3. DC Electrical Characteristics (Case temperature = 25 °C unless otherwise stated)

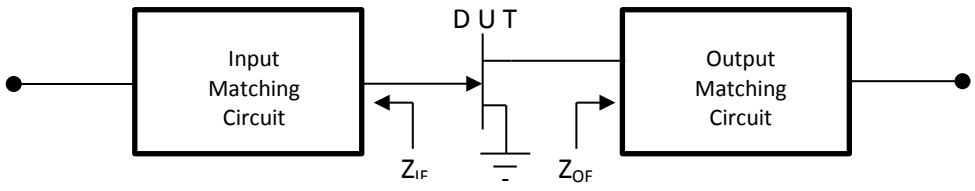
Parameter	Symbol	Min	Typ	Max	Units	Test Conditions
Gate Pinch-Off Voltage	V_P	-5.0			V	V_{DS} = 80V, I_{DS} = 1mA
Quiescent Gate Voltage	V_Q		-3.9		V	V_{DS} =80V, I_{DS} = 150mA

Table 4. Thermal Resistance (Case temperature = 30 °C unless otherwise stated)

Parameter	Symbol	Min	Typ	Max	Units	Test Conditions
Peak Thermal Resistance, Channel to Case	$R_{TH(JC)}$		0.17		°C/W	P_{diss} = 867W 300µs pulse length, 15% duty cycle V_{DS} = 80V

Table 5. Test Fixture Source & Load Impedances (Case temperature = 25 °C unless otherwise stated)

Frequency (GHz)	Z_{IF}	Z_{OF} Fundamental	Units	Test Conditions
2.9	2.75 - j 5.17	4.10 - j 4.33	Ω	P_{OUT} = 800W 300µs pulse length, 15% duty cycle V_{DS} = 80V, I_{DS} = 150mA
3.0	2.88 - j 3.87	5.35 - j 2.63	Ω	
3.1	3.14 - j 2.89	4.71 - j 1.09	Ω	



TYPICAL RF PERFORMANCE

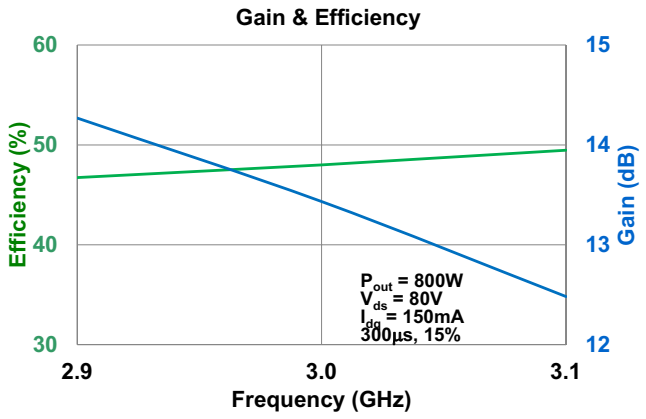


Figure 1

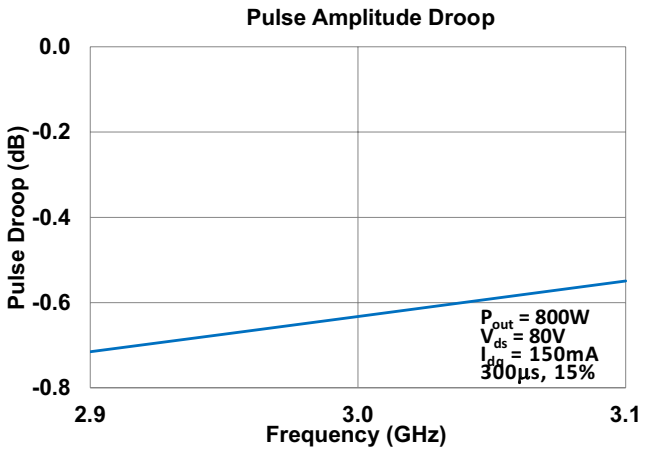


Figure 2

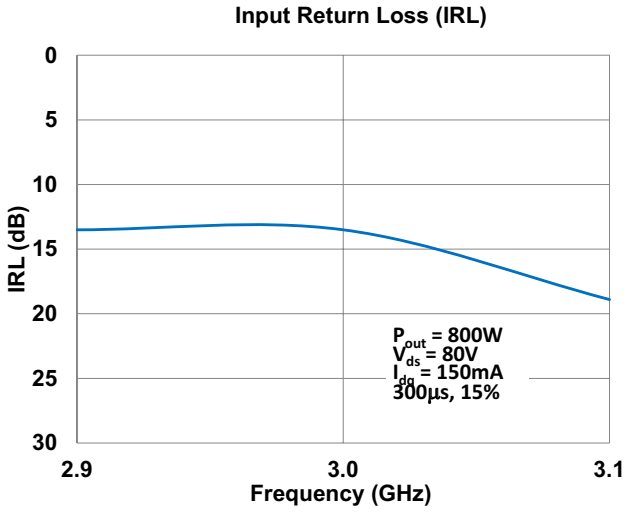


Figure 3

TYPICAL THERMAL PERFORMANCE

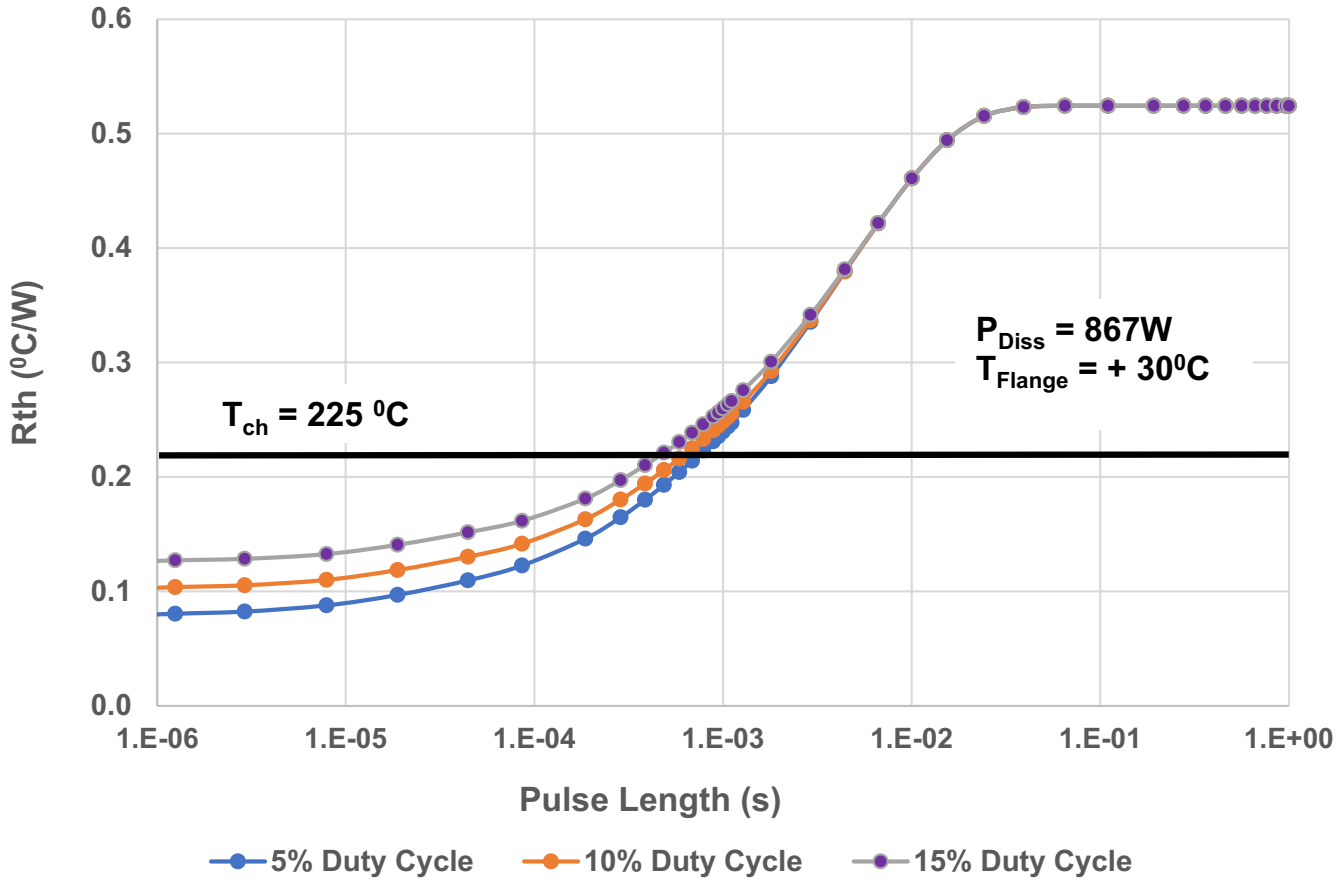
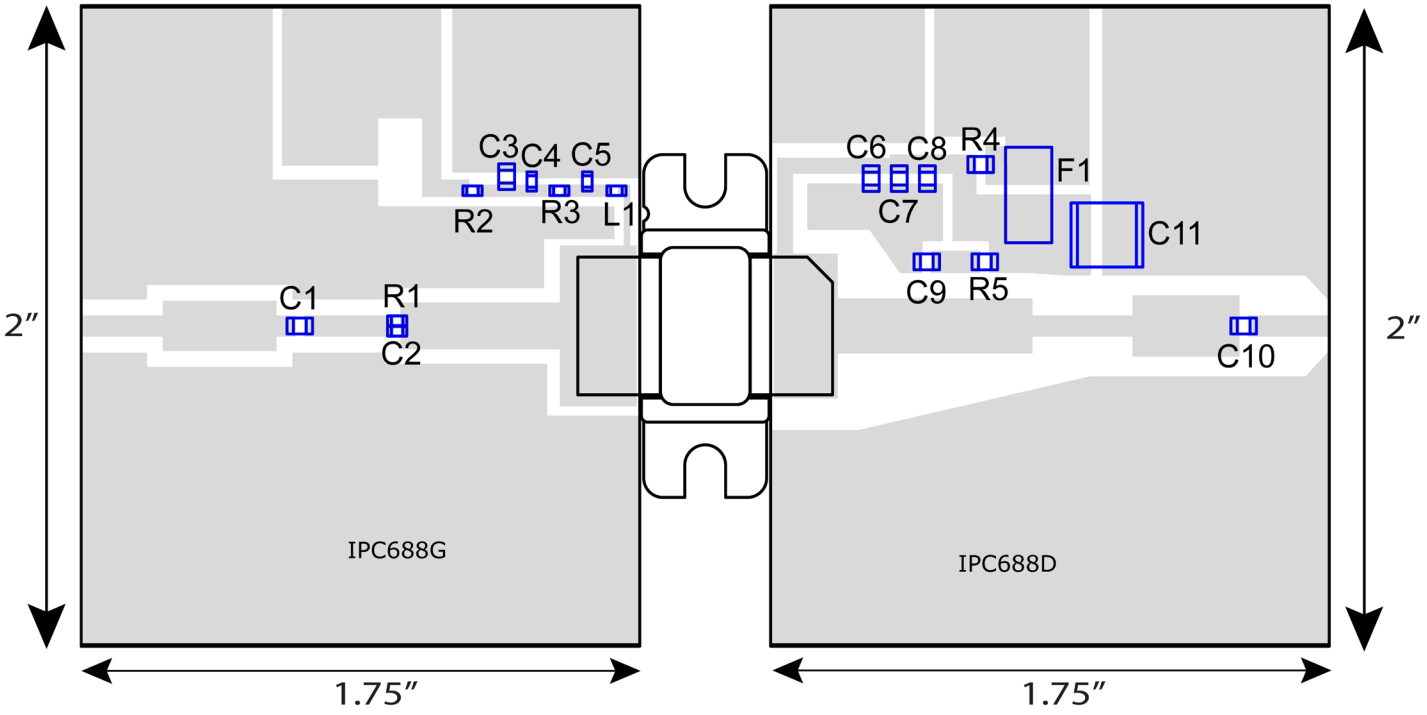


Figure 4

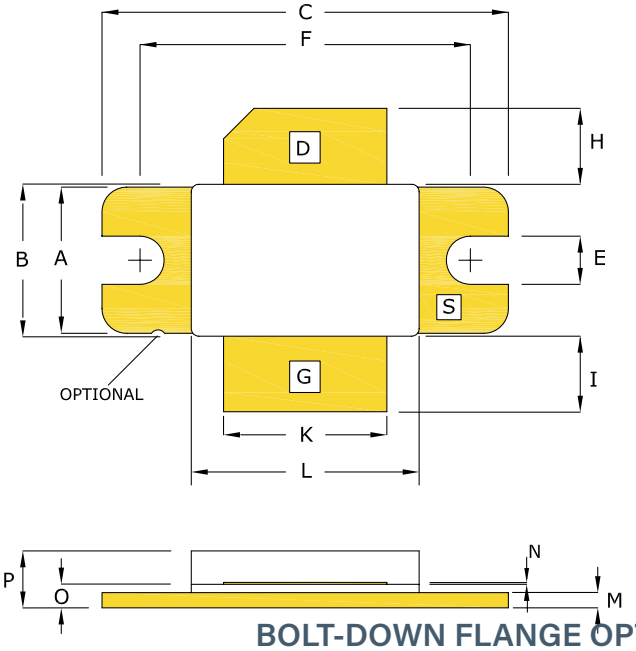
TEST FIXTURE



Bill of Materials for IGN2931M800 Test Fixture

Designator	Description	Quantity	Part Number
C1, C6, C10	CAP 15pF, 0805	3	600F150JT250XT
C2	CAP 15pF, 0603	1	600S150JT250XT
C3	CAP 1000pF, 0805	1	08051A102J4T2A1000
C4	CAP, 100pF, 0603	1	600S101JT250XT
C5	CAP 10pF, 0603	1	600S100JT250XT
C7	CAP 100pF, 0805	1	600F101JT250XT
C8, C9	CAP 0.1μF, 0805	2	08051C104K4T2A
C11	CAP 10μF, 2220	1	22201C106MAT2A
L1	IND 6.8nH, 0603	1	0603HP-6N8XJRW
R1	RES 100Ω, 0603	1	
R2,R3	RES 5.11Ω, 0603	1	
F1	FUSE 10A	1	CB61F10A-TR1
PC Board	30 mils, 1oz/1oz Copper	2	6035HTC-0300-H1/H1

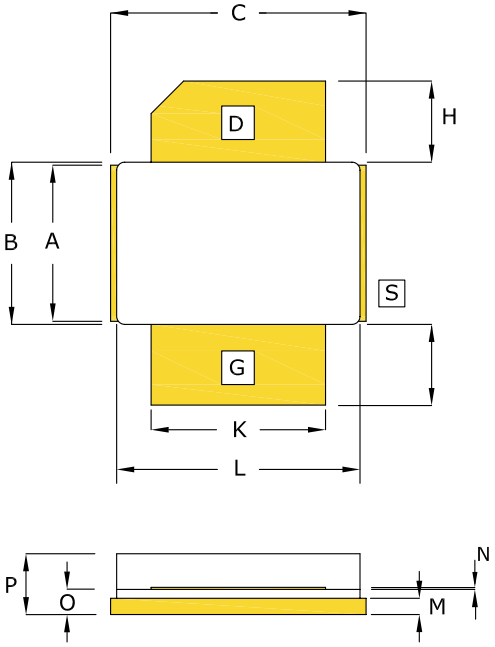
PACKAGE PL64B1



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.380	0.390	9.65	9.91
B	0.395	0.405	10.03	10.29
C	1.065	1.075	27.05	27.31
E	0.123	0.133	3.12	3.38
F	0.865	0.875	21.97	22.23
H	0.180	0.220	4.57	5.59
I	0.180	0.220	4.57	5.59
J	--	--	--	--
K	0.425	0.435	10.80	11.05
L	0.595	0.605	15.11	15.37
M	0.035	0.045	0.89	1.14
N	0.004	0.006	0.10	0.15
□	0.057	0.067	1.45	1.70
P	0.142	0.175	3.61	4.45

PIN SCHEDULE	
D	DRAIN
S	SOURCE
G	GATE

BOLT-DOWN FLANGE OPTION
IGN2931M800



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.380	0.390	9.65	9.91
B	0.395	0.405	10.03	10.29
C	0.625	0.635	15.88	16.13
E	--	--	--	--
F	--	--	--	--
H	0.180	0.220	4.57	5.59
I	0.180	0.220	4.57	5.59
J	--	--	--	--
K	0.425	0.435	10.80	11.05
L	0.595	0.605	15.11	15.37
M	0.035	0.045	0.89	1.14
N	0.004	0.006	0.10	0.15
□	0.057	0.067	1.45	1.70
P	0.142	0.175	3.61	4.45

PIN SCHEDULE	
D	DRAIN
S	SOURCE
G	GATE

EARLESS FLANGE OPTION
IGN2931M800S

ESD Rating

Parameter	Rating	Standard
ESD Human Body Model (HBM)	TBD	ESDA/JEDEC JS-001-2012
ESD Charged Device Model (CDM)	TBD	JEDEC JESD22-C11F
Moisture Sensitivty Level (MSL)	Unlimited Shelf Life	IPC/JEDEC J-STD-020

RoHS Compliance

Integra Technologies, Inc declares that its GaN and LDMOS Transistor Products comply with EU Directive 2011/65/EU on the restriction of the use of certain hazardous substances in electrical and electronic equipment (RoHS2), as adopted by EU member states on January 2, 2013 and amended on March 31, 2015 by EU Directive 2015/863/EU.

REACH Compliance

Integra Technologies supports EU Regulation number 1907/2006 concerning the Registration, Evaluation, Authorization, and Restriction of Chemicals (REACH) as these apply to Integra semiconductor products, development tools, and shipping packaging.

In support of the REACH regulation, Integra will:

- Inform customers and recipients of Integra product if they contain any substances that are of very high concern (SVHC) per the European Chemical Agency (ECHA) website.
- Notify ECHA if any Integra product that contains any SVHCs which exceed guidelines for REACH chemicals by weight per part number and for total content weight per year for all products produced in or imported to the European market.
- Cease shipments of product containing REACH Annex XIV substances until authorization has been obtained.
- Cease shipment of product containing REACH Annex XVII chemicals when restrictions apply.

Integra has evaluated its materials, BOMs, and product specifications and product and has determined that this transistor conforms to all REACH and SVHC regulations and guidelines. Integra has implemented actions and control programs that will assure continued compliance.

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DATA SHEET STATUS
Advanced Specification - This data sheet contains Advanced specifications.
Preliminary Specification - This data sheet contains specifications based on preliminary measurements and data.
Final Specification - This data sheet contains final product specifications.
MAXIMUM RATINGS Stress above one or more of the maximum ratings may cause permanent damage to the device. These are maximum ratings only operation of the device at these or at any other conditions above those given in the characteristics sections of the specification is not implied. Exposure to maximum values for extended periods of time may affect device reliability.

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